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PATENT ABSTRACTS OF JAPAN

(11)Publication number : 09-199758

(43)Date of publication of application : 31.07.1997

(51)Int.Cl.

H01L 33/00
H01L 21/205

(21)Application number : 08-007298

(71)Applicant : NEC CORP

(22)Date of filing : 19.01.1996

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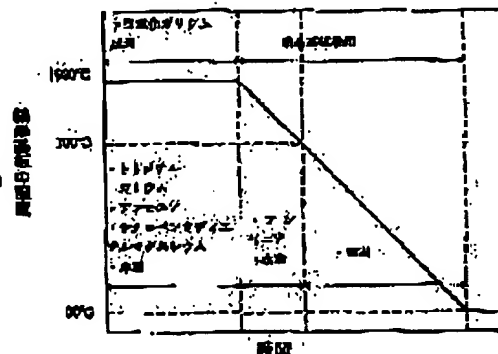
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(54) VAPOR GROWTH METHOD OF LOW-RESISTANCE P-TYPE GALLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a p-type gallium nitride-based compound with high crystal quality and low resistance without using an additional step in a vapor growth method suitable for mass product, by cooling a substrate crystal at a given temperature in atmosphere of carrier gas excluding hydrogen just after the crystal is grown in the vapor growth step.

SOLUTION: A crystal substrate including p-type gallium nitride has a temperature of 1030° C at a crystal growth step. When the crystal substrate is cooled after crystal growth, the vapor phase atmosphere is made of hydrogen carrier gas and ammonia at a temperature of 700° C or above, and at the temperature of 700° C the gas is changed to only nitrogen gas. The crystal surface is subjected to heat deterioration when the substrate is cooled at 700° C or below, and after the crystal is cooled, the gallium nitride-based compound semiconductor layer is etched and removed. Since the atmosphere includes only nitrogen when the substrate is cooled at 700° C or below, hydrogen gas is prevented from diffusing out of the crystal. After the cooling of the crystal, a desired structure is obtained only by etching the deteriorated crystal surface.



LEGAL STATUS

[Date of request for examination]

19.01.1996

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

2872096

[Date of registration]

08.01.1999

[Number of appeal against examiner's decision of rejection]

<http://www19.ipdl.ncipi.go.jp/PA1/result/detail/main/wAAAUFai.BDA409199758P...> 2005/11/17